

P-Channel 100V MOSFET

E38P100KH

V _{DS} (V)	$R_{DS(on),max}$ (m Ω)	I _D (A)	
-100	50@ V _{GS} = -10V	-38	

Features

- Trench MOS technology
- Low Rds(on),Low Qg
- Excellent Gate Charge x Rds(ON) Product (FOM)

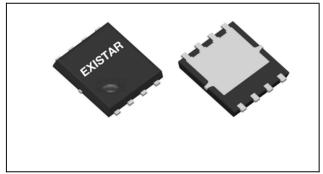
Applications

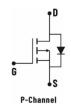
Fast switching

Package and ordering information

Ordering code	Package	Device code
E38P100KH	PDFN5*6	

PDFN5*6







Absolute Maximum Ratings T _A =25°C unless otherwise noted					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage		V_{DS}	-100	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous drain current	TC=25°C	lo	-38	A	
	TC=100°C	lo	-18	А	
Drain Current – Pulsed		I _{DM}	-120	А	
Maximum Power Dissipation		Po	104	W	
Single pulse avalanche energy		E _{AS}	285	mJ	
Junction and Storage Temperature Range		ТЈ ,Тѕтс	-55 To 150	$^{\circ}\! \mathbb{C}$	

Thermal Characteristics				
Parameter	Symbol	Тур	Max	Unit
Thermal Resistance junction-case	Rejc		1.2	°C /W
Thermal Resistance junction-to-Ambient	Reja		62	°C /W

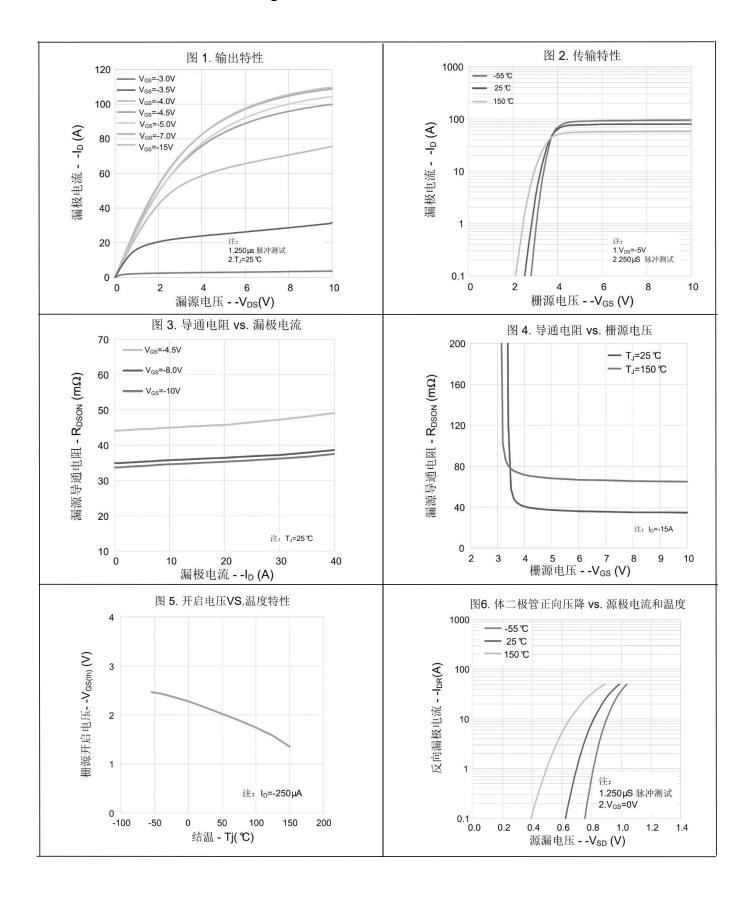
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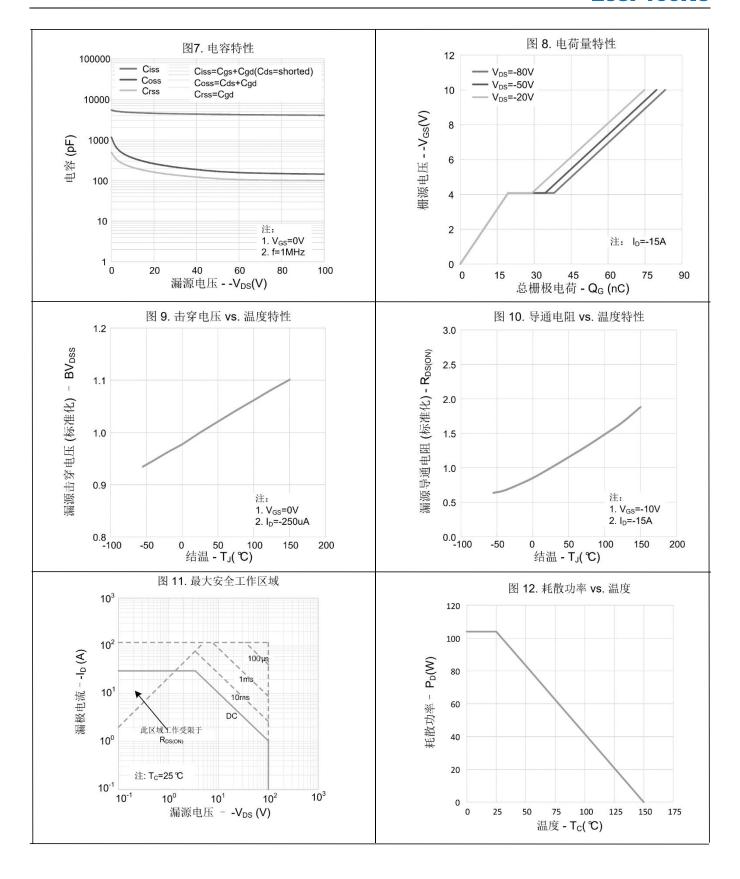
Electrical Characteristics(TJ=25 ℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Тур	Max	Unit
STATICPAR	RAME TERS					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V,I _D =-250μA	-100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-100V,V _{GS} =0V			-1	μA
I _{GSS}	Gate-Body Leakage Current	V_{GS} =±20V, V_{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =-250μ A	-1.5	-1.9	-2.5	V
В	Drain-Source On-State	V _{GS} =-10V, I _D =-6A		35	50	mΩ
R _{DS(ON)}	Resistance	V _{GS} =-4.5V,I _D =-5A		42	60	mΩ
gfs	Forward Transconductance	V _{DS} =-5V, I _D =-5A		23		S
DYNAMICP	ARAMET ERS					
C _{iss}	Input Capacitance			4387		pF
C _{oss}	Output Capacitance	V _{DS} =-25V,V _{GS} =0V, F=1.0MHz		228		pF
C _{rss}	Reverse Transfer Capacitance			150		pF
SWITCHING	SWITCHINGPARAMETER S					
t _{d(on)}	Turn-on Delay Time			10		nS
t _r	Turn-on Rise Time	V_{DD} =-50V, I_{D} =-15A, V_{GS} =-10V, R_{G} =9.1 Ω		41		nS
t _{d(off)}	Turn-Off Delay Time	GS 10 V, 1(G - 3.122		245		nS
t _f	Turn-Off Fall Time			87		nS
Qg	Total Gate Charge	V _{DS} =-50V,I _D =-15A, V _{GS} =0到-10V		81		nC
Q _{gs}	Gate-Source Charge			18		nC
Q_{gd}	Gate-Drain Charge			14.5		nC
V _{SD}	Diode Forward Voltage	V _{GS} =0V,I _{SD} =-1A			-1.4	V



Electrical Characteristics Diagrams

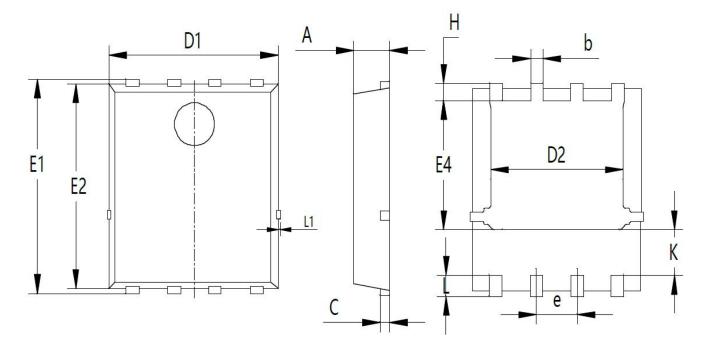








Package Outline Dimensions



Symbol		mm		
	Min	Nom	Max	
Α	1.00	1.10	1.20	
b	0.30	0.40	0.50	
С	0.154	0.254	0.354	
D1	5.00	5.20	5.40	
D2	3.80	4.10	4.25	
е	1.17	1.27	1.37	
E1	5.95	6.15	6.35	
E2	5.66	5.86	6.06	
E4	3.52	3.72	3.92	
Н	0.40	0.50	0.60	
L	0.30	0.60 0.70		
L1	0.12 REF			
K	1.15	1.30 1.45		



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